NSN 5961-01-332-5725

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-332-5725 **Inclosure Material:** Metal **Overall Length:** 1.253 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-5 **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.667 inches and 0.687 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 125.0 repetitive peak reverse voltage, peak total value and 90.0 reverse voltage, instantaneous **Current Rating Per Characteristic:** 50.00 amperes forward current, average absolute and 150.00 amperes source cutoff current outside diameter and 450.00 amperes forward current, average preset **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 1 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: